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(54) **METHOD OF FABRICATING SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

A method of fabricating a semiconductor device including: alternately stacking first interlayer insulating layers and first sacrificial layers on a substrate to form a first mold structure; forming a dummy hole penetrating the first mold structure; forming a dummy sacrificial pillar in the dummy hole, wherein the formation of the dummy sacrificial pillar includes forming a first recessed key region to expose a portion of an inner side surface of the dummy hole; and forming a second mold structure with a substantially uniform thickness on the first recessed key region and the first mold structure, wherein a top surface of the second mold structure has a second recessed key region corresponding to the first recessed key region.

